

#1 1/2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Inventors: Katsuji Iguchi, Sheng Teng Hsu,
Yoshi Ono and Jer-shen Maa

Serial No.: Not Yet Assigned

Filed: Herewith

Title: METHOD OF FABRICATING
DEEP SUB-MICRON CMOS
SOURCE/DRAIN WITH MDD
AND SELECTIVE CVD SILICIDE

PATENT APPLICATION

Attorney Docket No.
SLA 0636

JCS42 U.S. PTO
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Honorable Commissioner for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to
37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by
the Examiner and made of record in the above-identified application.

Oct 25 2001
(Date)

Respectfully submitted,

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Disclosure SLA0636